

## Inverter Grade Thyristors (Hockey PUK Version), 940 A



TO-200AC (B-PUK)

### FEATURES

- Metal case with ceramic insulator
- All diffused design
- Center amplifying gate
- Guaranteed high dV/dt
- Guaranteed high dI/dt
- International standard case TO-200AC (B-PUK)
- High surge current capability
- Low thermal impedance
- High speed performance
- Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



**RoHS  
COMPLIANT**

| PRODUCT SUMMARY    |                  |
|--------------------|------------------|
| Package            | TO-200AC (B-PUK) |
| Diode variation    | Single SCR       |
| $I_{T(AV)}$        | 940 A            |
| $V_{DRM}/V_{RRM}$  | 400 V, 800 V     |
| $V_{TM}$           | 1.63 V           |
| $I_{TSM}$ at 50 Hz | 20 000 A         |
| $I_{TSM}$ at 60 Hz | 20 950 A         |
| $I_{GT}$           | 200 mA           |
| $T_C/T_{hs}$       | 55 °C            |

### TYPICAL APPLICATIONS

- Inverters
- Choppers
- Induction heating
- All types of force-commutated converters

| MAJOR RATINGS AND CHARACTERISTICS |                 |             |                   |
|-----------------------------------|-----------------|-------------|-------------------|
| PARAMETER                         | TEST CONDITIONS | VALUES      | UNITS             |
| $I_{T(AV)}$                       |                 | 940         | A                 |
|                                   | $T_{hs}$        | 55          | °C                |
| $I_{T(RMS)}$                      |                 | 1900        | A                 |
|                                   | $T_{hs}$        | 25          | °C                |
| $I_{TSM}$                         | 50 Hz           | 20 000      | A                 |
|                                   | 60 Hz           | 20 950      |                   |
| $I^2t$                            | 50 Hz           | 2000        | kA <sup>2</sup> s |
|                                   | 60 Hz           | 1820        |                   |
| $V_{DRM}/V_{RRM}$                 |                 | 400 to 800  | V                 |
| $t_q$                             | Range           | 10 to 20    | µs                |
| $T_J$                             |                 | -40 to +125 | °C                |

### ELECTRICAL SPECIFICATIONS

| VOLTAGE RATINGS |              |  |  |  |
|-----------------|--------------|--|--|--|
| TYPE NUMBER     | VOLTAGE CODE | $V_{DRM}/V_{RRM}$ , MAXIMUM REPETITIVE PEAK VOLTAGE<br>V | $V_{RSM}$ , MAXIMUM NON-REPETITIVE PEAK VOLTAGE<br>V | $I_{DRM}/I_{RRM}$ MAXIMUM AT $T_J = T_J$ MAXIMUM<br>mA |
| VS-ST733C..L    | 04           | 400  | 500  | 75   |
|                 | 08           | 800  | 900  |  |



| CURRENT CARRYING CAPABILITY      |           |      |           |      |           |      |       |
|----------------------------------|-----------|------|-----------|------|-----------|------|-------|
| FREQUENCY                        |           |      |           |      |           |      | UNITS |
| 50 Hz                            | 2200      | 1900 | 3580      | 3100 | 6800      | 5920 | A     |
| 400 Hz                           | 2050      | 1660 | 3600      | 3130 | 3750      | 3240 |       |
| 1000 Hz                          | 1370      | 1070 | 2900      | 2450 | 2120      | 1780 |       |
| 2500 Hz                          | 500       | 370  | 1220      | 980  | 960       | 770  |       |
| Recovery voltage $V_R$           | 50        |      | 50        |      | 50        |      | V     |
| Voltage before turn-on $V_D$     | $V_{DRM}$ |      | $V_{DRM}$ |      | $V_{DRM}$ |      |       |
| Rise of on-state current $dI/dt$ | 50        |      | -         |      | -         |      | A/μs  |
| Heatsink temperature             | 40        | 55   | 40        | 55   | 40        | 55   | °C    |
| Equivalent values for RC circuit | 10/0.47   |      | 10/0.47   |      | 10/0.47   |      | Ω/μF  |

| ABSOLUTE MAXIMUM RATINGS                                   |               |  |                            |           |                    |
|--|---------------|--|----------------------------|-----------|--------------------|
| PARAMETER  | SYMBOL        | TEST CONDITIONS  |                            | VALUES    | UNITS              |
| Maximum average on-state current at heatsink temperature   | $I_{T(AV)}$   | 180° conduction, half sine wave double side (single side) cooled                         |                            | 940 (350) | A                  |
|  |               |  |                            | 55 (85)   | °C                 |
| Maximum RMS on-state current                               | $I_{T(RMS)}$  | DC at 25 °C heatsink temperature double side cooled                                      |                            | 1900      | A                  |
| Maximum peak, one half cycle, non-repetitive surge current | $I_{TSM}$     | t = 10 ms  | No voltage reappplied      | 20 000    |                    |
|  |               | t = 8.3 ms   |                            | 20 950    |                    |
|  |               | t = 10 ms  | 100 % $V_{RRM}$ reappplied | 16 800    |                    |
|  |               | t = 8.3 ms   |                            | 17 600    |                    |
| Maximum $I^2t$ for fusing                                  | $I^2t$        | t = 10 ms  | No voltage reappplied      | 2000      | kA <sup>2</sup> s  |
|  |               | t = 8.3 ms   |                            | 1820      |                    |
|  |               | t = 10 ms  | 100 % $V_{RRM}$ reappplied | 1410      |                    |
|  |               | t = 8.3 ms   |                            | 1290      |                    |
| Maximum $I^2\sqrt{t}$ for fusing                           | $I^2\sqrt{t}$ | t = 0.1 ms to 10 ms, no voltage reappplied   |                            | 20 000    | kA <sup>2</sup> √s |
| Maximum peak on-state voltage                              | $V_{TM}$      | $I_{TM} = 1700$ A, $T_J = T_J$ maximum, $t_p = 10$ ms sine wave pulse                    |                            | 1.63      | V                  |
| Low level value of threshold voltage                       | $V_{T(TO)1}$  | $(16.7 \% \times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)})$ , $T_J = T_J$ maximum |                            | 1.09      |                    |
| High level value of threshold voltage                      | $V_{T(TO)2}$  | $(I > \pi \times I_{T(AV)})$ , $T_J = T_J$ maximum                                       |                            | 1.20      |                    |
| Low level value of forward slope resistance                | $r_{t1}$      | $(16.7 \% \times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)})$ , $T_J = T_J$ maximum |                            | 0.32      | mΩ                 |
| High level value of forward slope resistance               | $r_{t2}$      | $(I > \pi \times I_{T(AV)})$ , $T_J = T_J$ maximum                                       |                            | 0.29      |                    |
| Maximum holding current                                    | $I_H$         | $T_J = 25$ °C, $I_T > 30$ A  |                            | 600       | mA                 |
| Typical latching current                                   | $I_L$         | $T_J = 25$ °C, $V_A = 12$ V, $R_a = 6$ Ω, $I_G = 1$ A                                    |                            | 1000      |                    |



| SWITCHING  |                |   |        |       |
|--|----------------|---|--------|-------|
| PARAMETER  | SYMBOL         | TEST CONDITIONS   | VALUES | UNITS |
| Maximum non-repetitive rate of rise of turned-on current | di/dt          | T <sub>J</sub> = T <sub>J</sub> maximum, V <sub>DRM</sub> = Rated V <sub>DRM</sub> , I <sub>TM</sub> = 2 x di/dt<br>Gate pulse: 20 V 20 Ω, 10 μs 0.5 μs rise time                 | 1000   | A/μs  |
| Typical delay time                                       | t <sub>d</sub> | T <sub>J</sub> = 25 °C, V <sub>DM</sub> = Rated V <sub>DRM</sub> , I <sub>TM</sub> = 50 A DC, t <sub>p</sub> = 1 μs<br>Resistive load, gate pulse: 10 V, 5 Ω source               | 1.5    | μs    |
| Maximum turn-off time                                    | minimum        | T <sub>J</sub> = T <sub>J</sub> maximum, I <sub>TM</sub> = 550 A, commutating di/dt = 40 A/μs,<br>V <sub>R</sub> = 50 V, t <sub>p</sub> = 500 μs, dV/dt: see table in device code | 10     |       |
|  | maximum        |   | 20     |       |

| BLOCKING   |  |   |        |       |
|--|--|---|--------|-------|
| PARAMETER  | SYMBOL                                 | TEST CONDITIONS   | VALUES | UNITS |
| Maximum critical rate of rise of off-state voltage | dV/dt                                  | T <sub>J</sub> = T <sub>J</sub> maximum, linear to 80 % V <sub>DRM</sub> ,<br>higher value available on request | 500    | V/μs  |
| Maximum peak reverse and off-state leakage current | I <sub>RRM</sub> ,<br>I <sub>DRM</sub> | T <sub>J</sub> = T <sub>J</sub> maximum, rated V <sub>DRM</sub> /V <sub>RRM</sub> applied                       | 75     | mA    |

| TRIGGERING                                  |                    |   |        |       |
|---|--------------------|---|--------|-------|
| PARAMETER                                   | SYMBOL             | TEST CONDITIONS   | VALUES | UNITS |
| Maximum peak gate power                     | P <sub>GM</sub>    | T <sub>J</sub> = T <sub>J</sub> maximum, f = 50 Hz, d% = 50             | 60     | W     |
| Maximum average gate power                  | P <sub>G(AV)</sub> |   | 10     |       |
| Maximum peak positive gate current          | I <sub>GM</sub>    | T <sub>J</sub> = T <sub>J</sub> maximum, t <sub>p</sub> ≤ 5 ms          | 10     | A     |
| Maximum peak positive gate voltage          | +V <sub>GM</sub>   |   | 20     | V     |
| Maximum peak negative gate voltage          | -V <sub>GM</sub>   |   | 5      |       |
| Maximum DC gate current required to trigger | I <sub>GT</sub>    | T <sub>J</sub> = 25 °C, V <sub>A</sub> = 12 V, R <sub>a</sub> = 6 Ω     | 200    | mA    |
| Maximum DC gate voltage required to trigger | V <sub>GT</sub>    |   | 3      | V     |
| Maximum DC gate current not to trigger      | I <sub>GD</sub>    | T <sub>J</sub> = T <sub>J</sub> maximum, rated V <sub>DRM</sub> applied | 20     | mA    |
| Maximum DC gate voltage not to trigger      | V <sub>GD</sub>    |   | 0.25   | V     |

| THERMAL AND MECHANICAL SPECIFICATIONS            |                     |   |                  |           |
|--|---------------------|---|------------------|-----------|
| PARAMETER  | SYMBOL              | TEST CONDITIONS                               | VALUES           | UNITS     |
| Maximum operating junction temperature range     | T <sub>J</sub>      |   | -40 to +125      | °C        |
| Maximum storage temperature range                | T <sub>Stg</sub>    |   | -40 to +150      |           |
| Maximum thermal resistance, junction to heatsink | R <sub>thJ-hs</sub> | DC operation single side cooled               | 0.073            | K/W       |
|  |                     | DC operation double side cooled               | 0.031            |           |
| Maximum thermal resistance, case to heatsink     | R <sub>thC-hs</sub> | DC operation single side cooled               | 0.011            |           |
|  |                     | DC operation double side cooled               | 0.005            |           |
| Mounting force, ± 10 %                           |                     |   | 14 700<br>(1500) | N<br>(kg) |
| Approximate weight                               |                     |   | 255              | g         |
| Case style                                       |                     | See dimensions - link at the end of datasheet | TO-200AC (B-PUK) |           |



| $\Delta R_{thJ-hs}$ CONDUCTION |                       |             |                        |             |   |       |
|--------------------------------|-----------------------|-------------|------------------------|-------------|---|-------|
| CONDUCTION ANGLE               | SINUSOIDAL CONDUCTION |             | RECTANGULAR CONDUCTION |             | TEST CONDITIONS                         | UNITS |
|                                | SINGLE SIDE           | DOUBLE SIDE | SINGLE SIDE            | DOUBLE SIDE |   |       |
| 180°                           | 0.009                 | 0.009       | 0.006                  | 0.006       | T <sub>J</sub> = T <sub>J</sub> maximum | K/W   |
| 120°                           | 0.011                 | 0.011       | 0.011                  | 0.011       |   |       |
| 90°                            | 0.014                 | 0.014       | 0.015                  | 0.015       |   |       |
| 60°                            | 0.020                 | 0.021       | 0.021                  | 0.022       |   |       |
| 30°                            | 0.036                 | 0.036       | 0.036                  | 0.036       |   |       |

**Note**

- The table above shows the increment of thermal resistance  $R_{thJ-hs}$  when devices operate at different conduction angles than DC

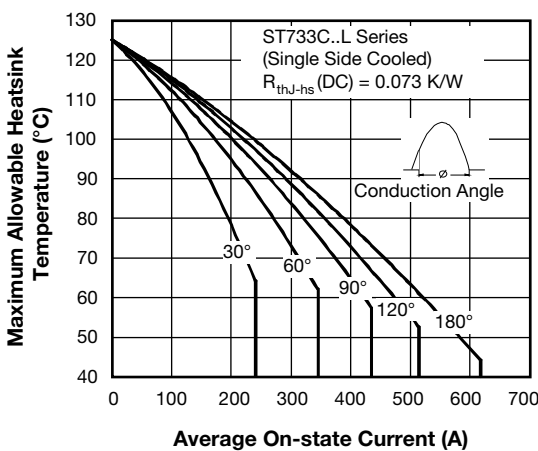


Fig. 1 - Current Ratings Characteristics

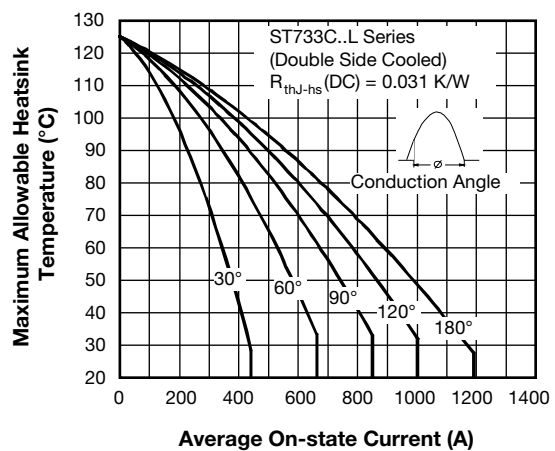


Fig. 3 - Current Ratings Characteristics

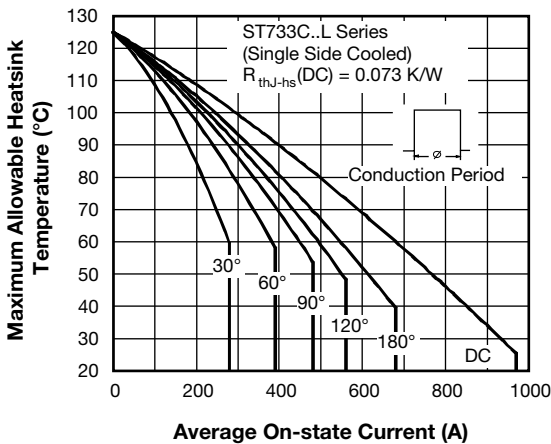


Fig. 2 - Current Ratings Characteristics

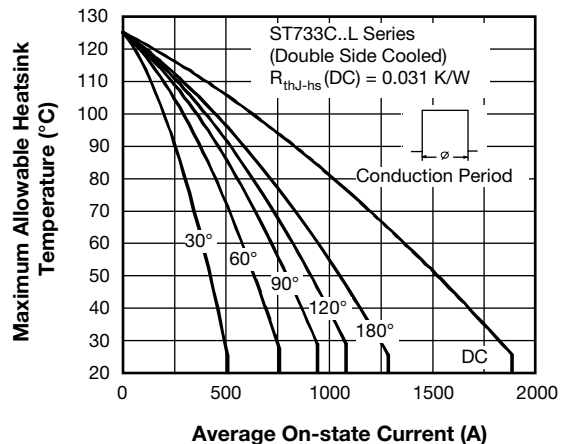


Fig. 4 - Current Ratings Characteristics

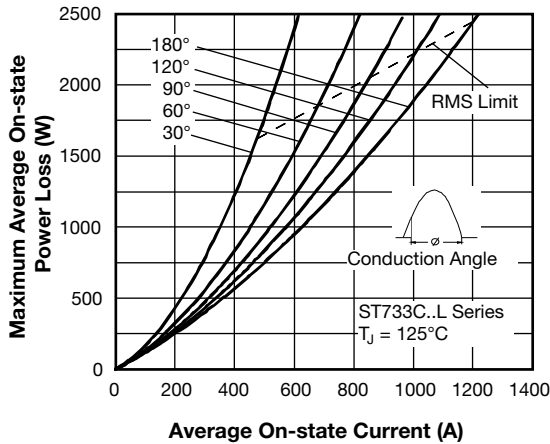


Fig. 5 - On-State Power Loss Characteristics

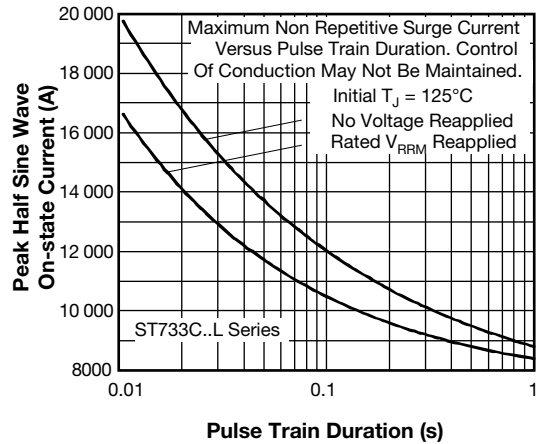


Fig. 8 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

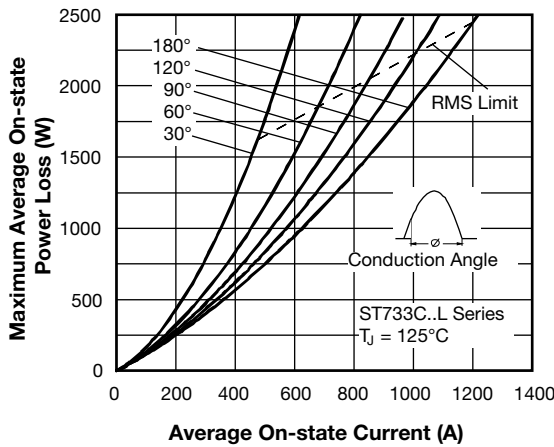


Fig. 6 - On-State Power Loss Characteristics

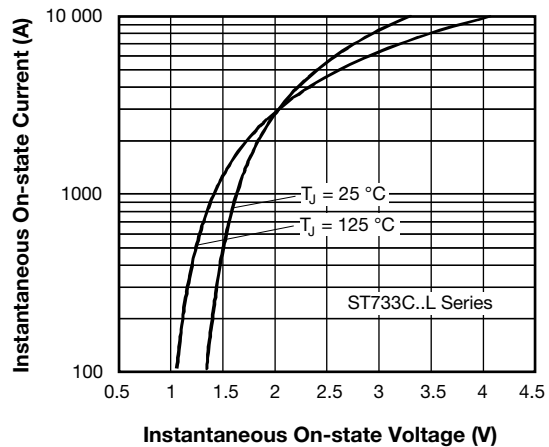


Fig. 9 - On-State Voltage Drop Characteristics

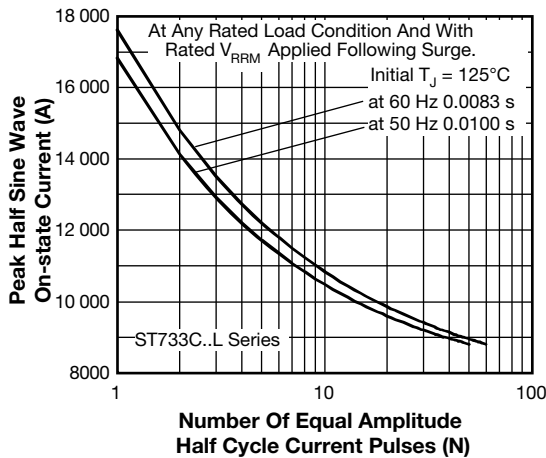


Fig. 7 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

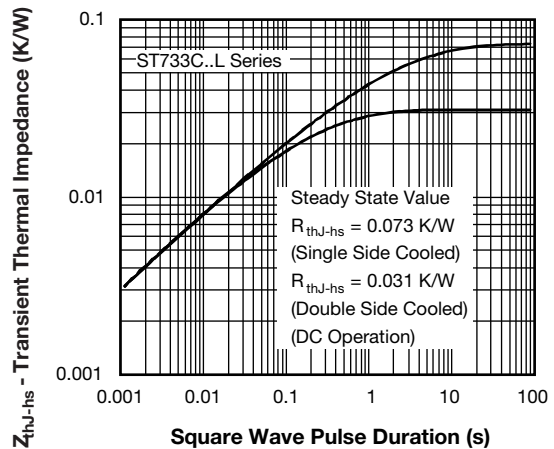


Fig. 10 - Thermal Impedance  $Z_{thJC}$  Characteristics

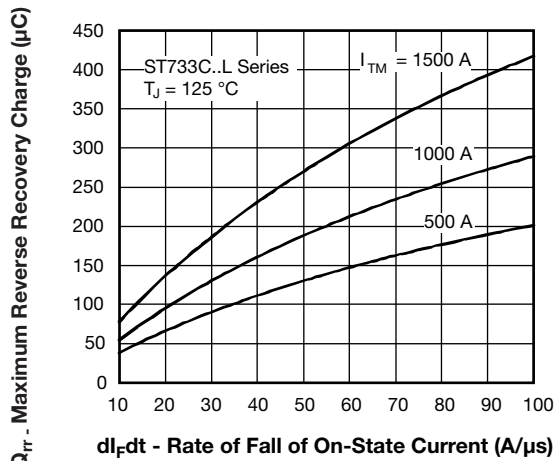


Fig. 11 - Reverse Recovered Charge Characteristics

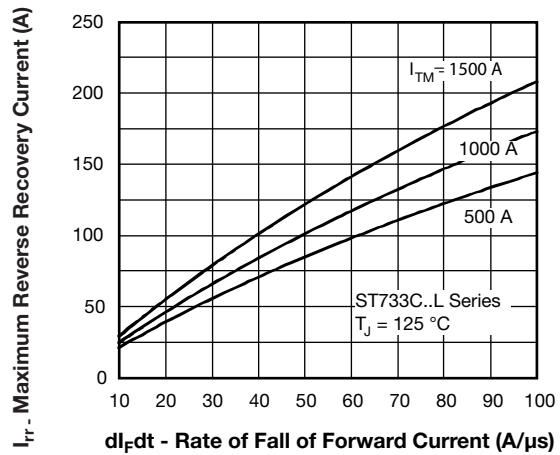


Fig. 12 - Reverse Recovered Current Characteristics

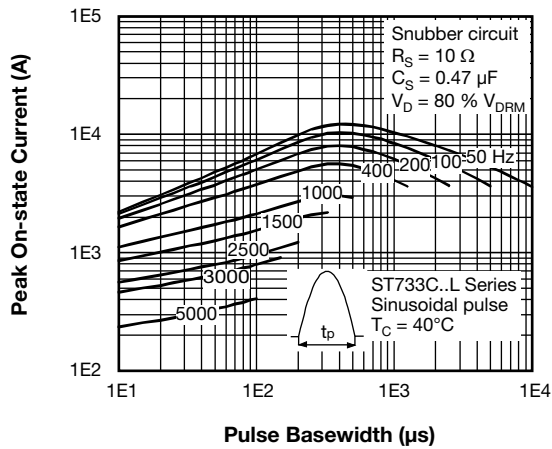


Fig. 13 - Frequency Characteristics

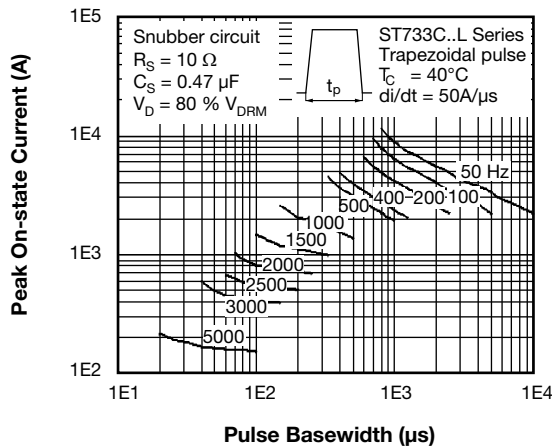
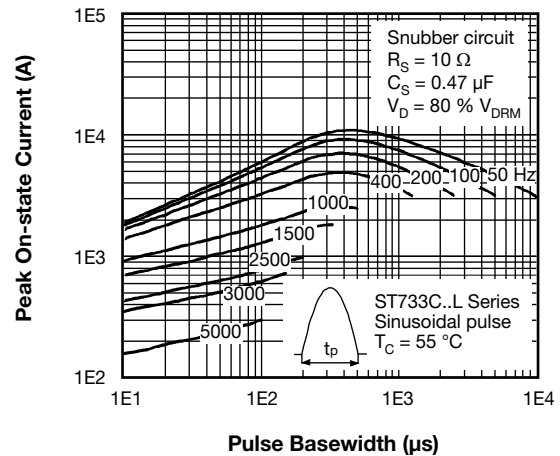
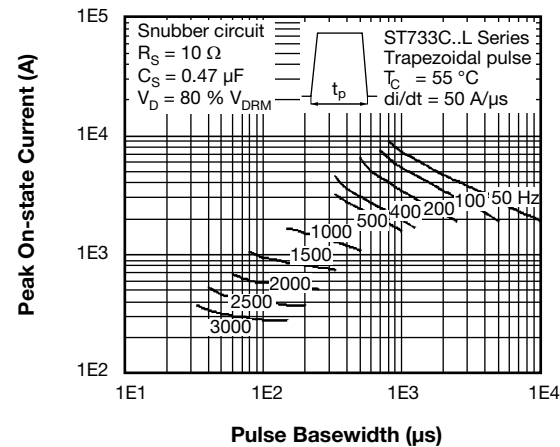


Fig. 14 - Frequency Characteristics



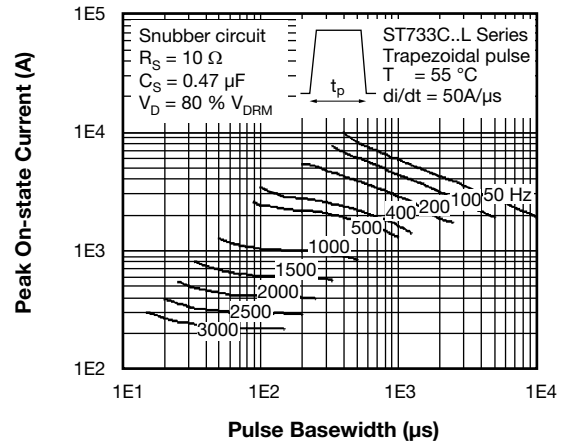
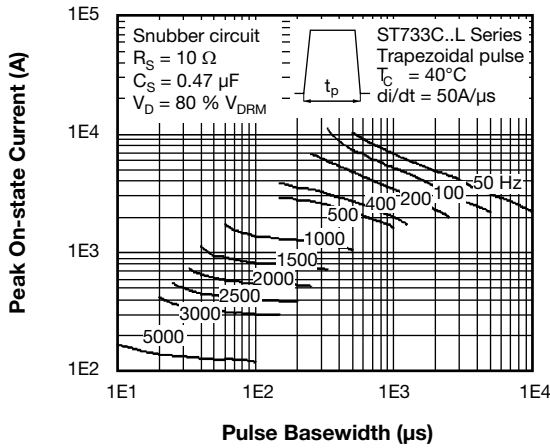


Fig. 15 - Frequency Characteristics

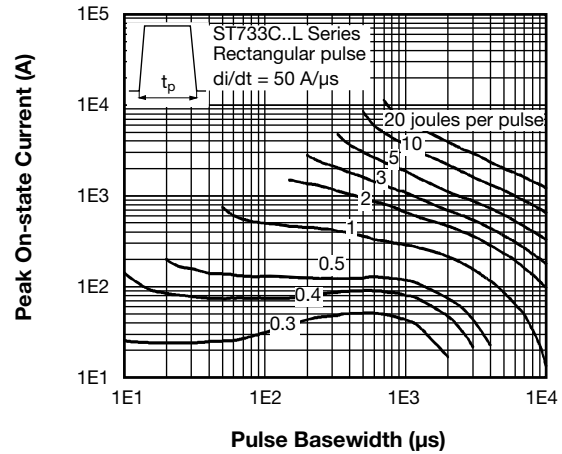
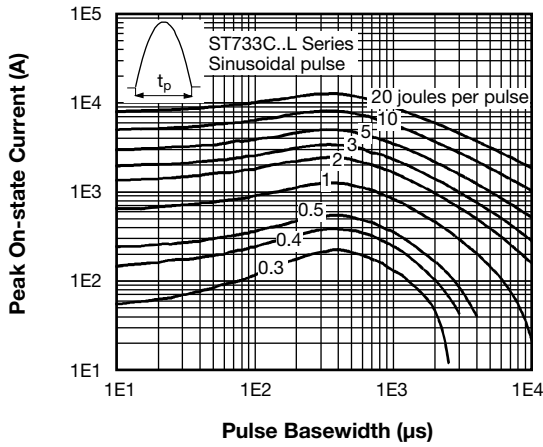


Fig. 16 - Maximum On-State Energy Power Loss Characteristics

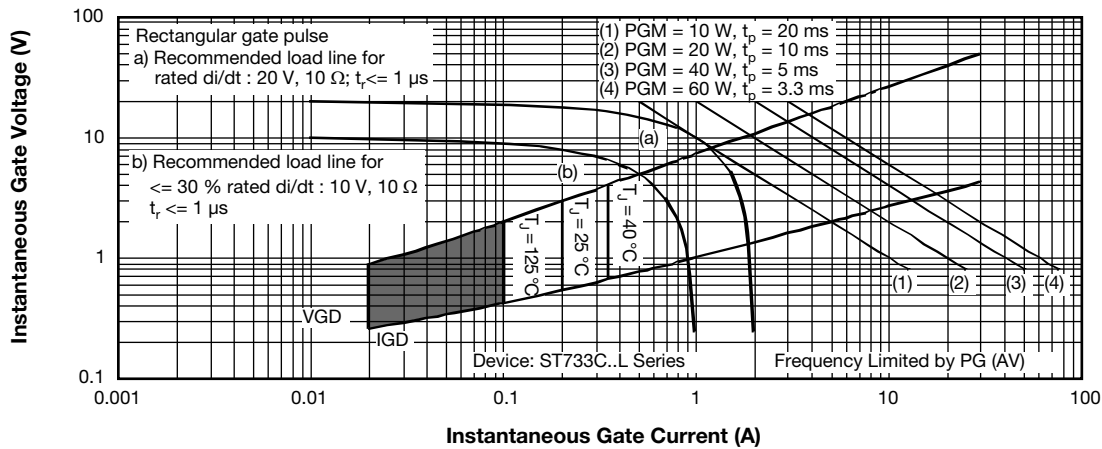


Fig. 17 - Gate Characteristics



## ORDERING INFORMATION TABLE

|             |            |           |           |          |          |           |          |          |          |          |          |
|-------------|------------|-----------|-----------|----------|----------|-----------|----------|----------|----------|----------|----------|
| Device code | <b>VS-</b> | <b>ST</b> | <b>73</b> | <b>3</b> | <b>C</b> | <b>08</b> | <b>L</b> | <b>H</b> | <b>K</b> | <b>1</b> | <b>-</b> |
|             | ①          | ②         | ③         | ④        | ⑤        | ⑥         | ⑦        | ⑧        | ⑨        | ⑩        | ⑪        |

- 1** - Vishay Semiconductors product
- 2** - Thyristor
- 3** - Essential part number
- 4** - 3 = fast turn-off
- 5** - C = ceramic PUK
- 6** - Voltage code x 100 =  $V_{RRM}$   
(see Voltage Ratings table)
- 7** - L = PUK case TO-200AC (B-PUK)
- 8** - Reapplied dV/dt code (for  $t_q$  test condition)
- 9** -  $t_q$  code
- 10** - 0 = eyelet terminals  
(gate and auxiliary cathode unsoldered leads)  
1 = fast-on terminals  
(gate and auxiliary cathode unsoldered leads)  
2 = eyelet terminals  
(gate and auxiliary cathode soldered leads)  
3 = fast-on terminals  
(gate and auxiliary cathode soldered leads)
- 11** - Critical dV/dt:
  - None = 500 V/ $\mu$ s (standard value)
  - L = 1000 V/ $\mu$ s (special selection)

| dV/dt - $t_q$ combinations available |                    |    |    |     |     |     |
|--------------------------------------|--------------------|----|----|-----|-----|-----|
|                                      | dV/dt (V/ $\mu$ s) | 20 | 50 | 100 | 200 | 400 |
| $t_q$ ( $\mu$ s)                     | 10                 | CN | DN | EN  | -   | -   |
|                                      | 12                 | CM | DM | EM  | FM* | -   |
|                                      | 15                 | CL | DL | EL  | FL* | HL  |
|                                      | 18                 | CP | DP | EP  | FP  | HP  |
|                                      | 20                 | CK | DK | EK  | FK  | H   |

\* Standard part number.  
All other types available only on request.

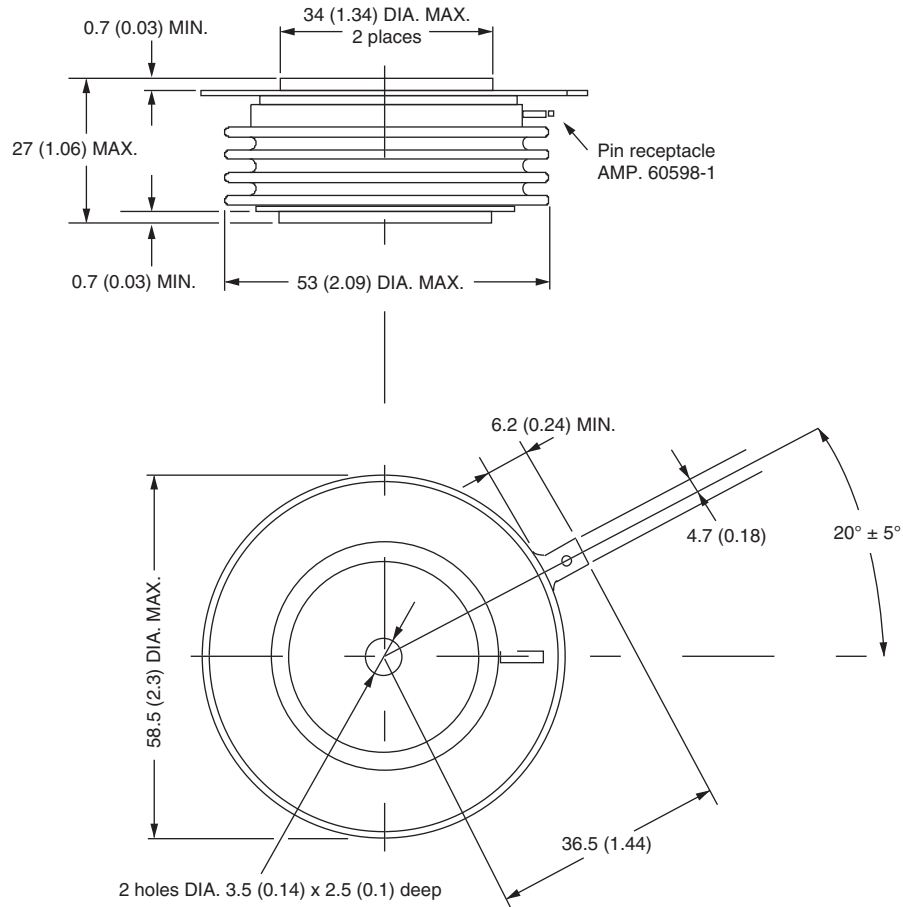
| LINKS TO RELATED DOCUMENTS |  |
|----------------------------|--|
| Dimensions                 | <a href="http://www.vishay.com/doc?95076">www.vishay.com/doc?95076</a> |



## TO-200AC (B-PUK)

**DIMENSIONS** in millimeters (inches)

Creepage distance: 36.33 (1.430) minimum  
 Strike distance: 17.43 (0.686) minimum



Quote between upper and lower pole pieces has to be considered after application of mounting force (see thermal and mechanical specification)



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- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- При необходимости вся продукция военного и аэрокосмического назначения проходит испытания и сертификацию в лаборатории (по согласованию с заказчиком);
- Поставка специализированных компонентов военного и аэрокосмического уровня качества (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Actel, Aeroflex, Peregrine, VPT, Syfer, Eurofarad, Texas Instruments, MS Kennedy, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Компания «Океан Электроники» является официальным дистрибьютором и эксклюзивным представителем в России одного из крупнейших производителей разъемов военного и аэрокосмического назначения «**JONHON**», а так же официальным дистрибьютором и эксклюзивным представителем в России производителя высокотехнологичных и надежных решений для передачи СВЧ сигналов «**FORSTAR**».



## JONHON

«**JONHON**» (основан в 1970 г.)

Разъемы специального, военного и аэрокосмического назначения:

(Применяются в военной, авиационной, аэрокосмической, морской, железнодорожной, горно- и нефтедобывающей отраслях промышленности)

«**FORSTAR**» (основан в 1998 г.)

ВЧ соединители, коаксиальные кабели,  
кабельные сборки и микроволновые компоненты:

(Применяются в телекоммуникациях гражданского и специального назначения, в средствах связи, РЛС, а так же военной, авиационной и аэрокосмической отраслях промышленности).



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